

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (Use several sheets if necessary)	ATTY DOCKET NO. 3531-0103P	APPLICATION NO. New
	APPLICANT Paul R. BERGER et al	
	FILING DATE August 21, 2001	GROUP

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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
					YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, etc.)

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